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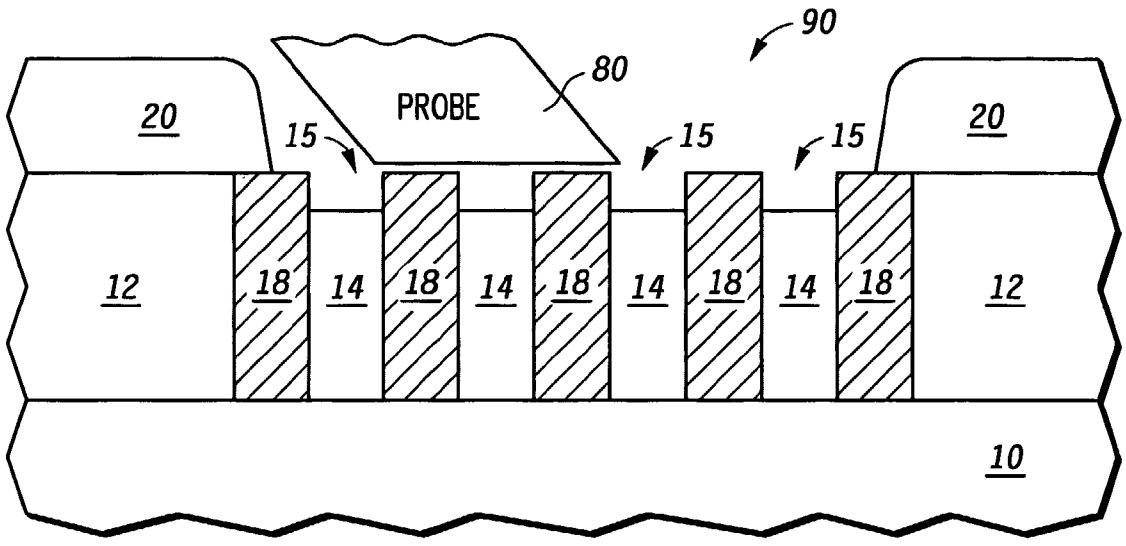
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(54) Title: METHOD OF FORMING A BOND PAD AND STRUCTURE THEREOF



(57) Abstract: A bond pad (100) is formed by first providing a planarized combination of copper (18) and silicon oxide features (14) in a bond pad region. The silicon oxide features (14) are etched back to provide a plurality recesses (15) in the copper in the bond pad region. A corrosion barrier (22) is formed over the copper and the silicon oxide features in the recesses. Probing of the wafer (10) is done by directly applying the probe to the copper. A wire bond (24) is directly attached to the copper (18). The probe (80) is prevented from penetrating all the way through the copper (18) because the recessed features (15) are present. With the recesses (15) in the copper, the wire bond (24) more readily breaks down and penetrates the corrosion barrier and is also less likely to slip on the bond pad (100).

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